Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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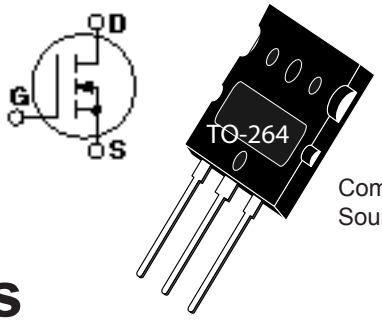
ARF469AG
ARF469BG



Common Source

RF POWER MOSFETs
N-CHANNEL ENHANCEMENT MODE

150V 350W 45MHz

The ARF469A and ARF469B comprise a symmetric pair of common source RF power transistors designed for push-pull scientific, commercial, medical and industrial RF power amplifier applications up to 45 MHz. They have been optimized for both linear and high efficiency classes of operation.

- **Specified 150 Volt, 40.68 MHz Characteristics:**
  - **Output Power = 350 Watts.**
  - **Gain = 16dB (Class AB)**
  - **Efficiency = 75% (Class C)**
- **Low Cost Common Source RF Package.**
- **Low Vth thermal coefficient.**
- **Low Thermal Resistance.**
- **Optimized SOA for Superior Ruggedness.**

MAXIMUM RATINGS

All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	Ratings	UNIT
V_{DSS}	Drain-Source Voltage	500	Volts
V_{DGO}	Drain-Gate Voltage	500	
I_D	Continuous Drain Current @ T_C = 25°C	30	Amps
V_{GS}	Gate-Source Voltage	±30	Volts
P_D	Total Power Dissipation @ T_C = 25°C	445	Watts
$R_{\theta JC}$	Junction to Case	0.28	°C/W
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage (V_{GS} = 0V, I_D = 250 µA)	500			Volts
$R_{DS(ON)}$	Drain-Source On-State Resistance ① (V_{GS} = 10V, I_D = 15A)		0.25	0.28	ohms
I_{DSS}	Zero Gate Voltage Drain Current (V_{DS} = 500V, V_{GS} = 0V)			25	µA
	Zero Gate Voltage Drain Current (V_{DS} = 400V, V_{GS} = 0V, T_C = 125°C)			250	
I_{GSS}	Gate-Source Leakage Current (V_{GS} = ±30V, V_{DS} = 0V)			±100	nA
g_{fs}	Forward Transconductance (V_{DS} = 25V, I_D = 6.5A)		8		mhos
$V_{GS}(TH)$	Gate Threshold Voltage (V_{DS} = V_{GS}, I_D = 1mA)	2		4	Volts

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	V_{GS} = 0V V_{DS} = 150V f = 1 MHz		2300		
C_{oss}	Output Capacitance			250		pF
C_{rss}	Reverse Transfer Capacitance			125		

FUNCTIONAL CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
G_{PS}	Common Source Amplifier Power Gain	f = 40.68 MHz	14	16		dB
η	Drain Efficiency	V_{GS} = 2.5V V_{DD} = 150V	70	75		%
Ψ	Electrical Ruggedness VSWR 10:1	P_{out} = 350W	No Degradation in Output Power			

① Pulse Test: Pulse width < 380μS, Duty Cycle < 2%

TYPICAL PERFORMANCE CURVES

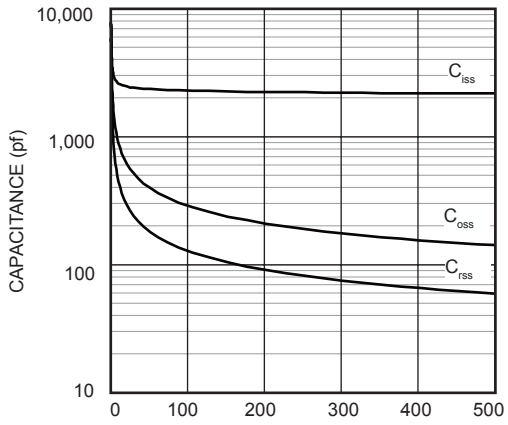


Figure 1, Typical Capacitance vs. Drain-to-Source Voltage

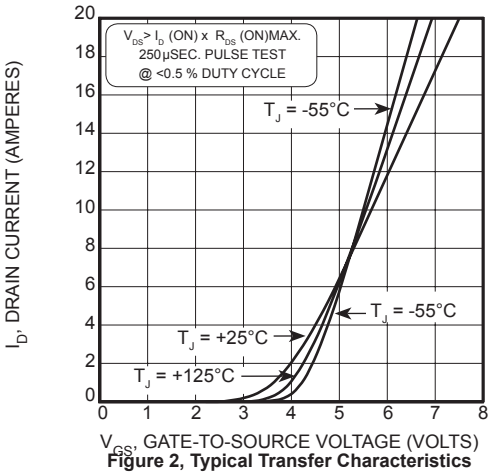


Figure 2, Typical Transfer Characteristics

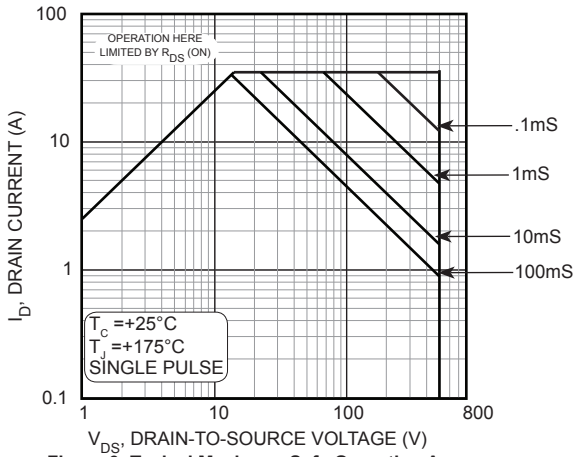


Figure 3, Typical Maximum Safe Operating Area

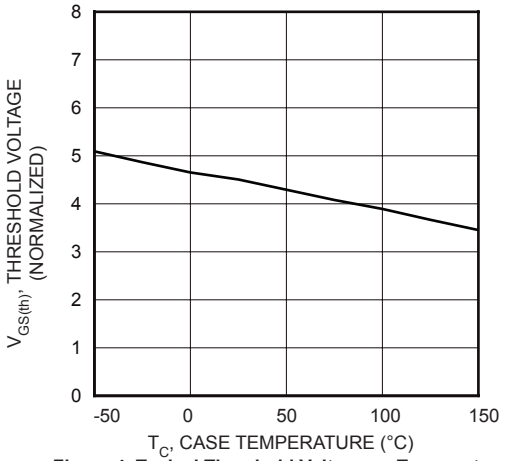


Figure 4, Typical Threshold Voltage vs Temperature

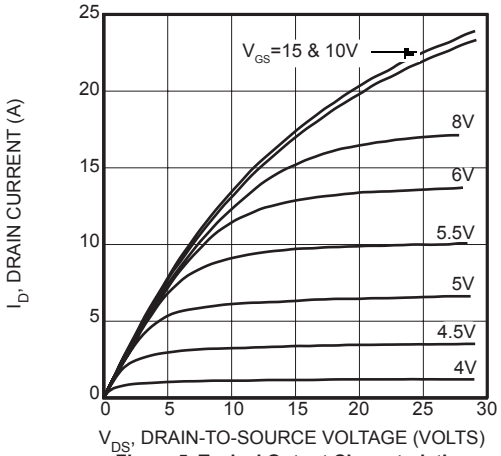


Figure 5, Typical Output Characteristics

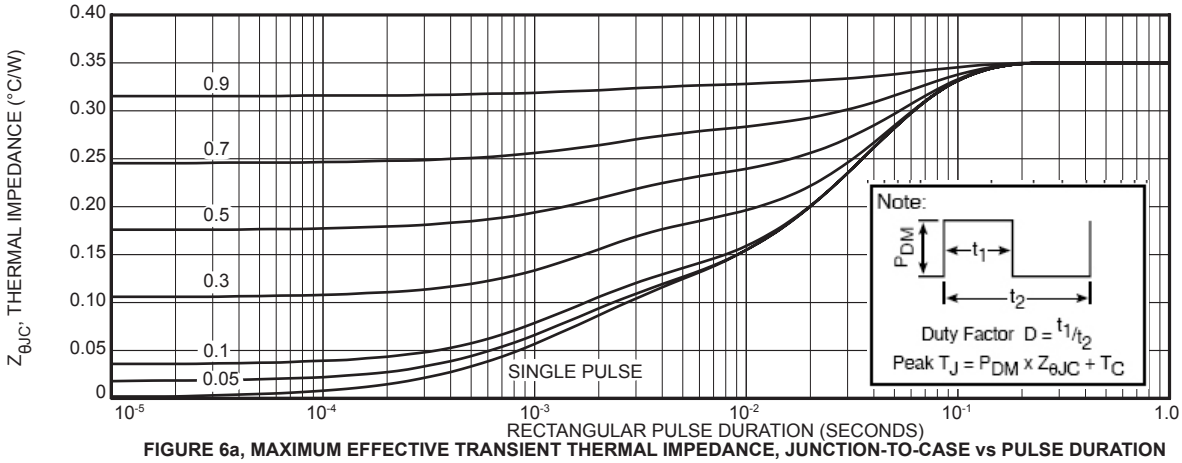


FIGURE 6a, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

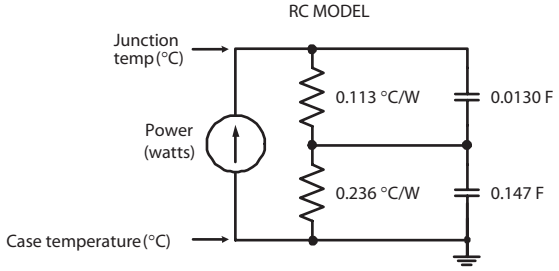
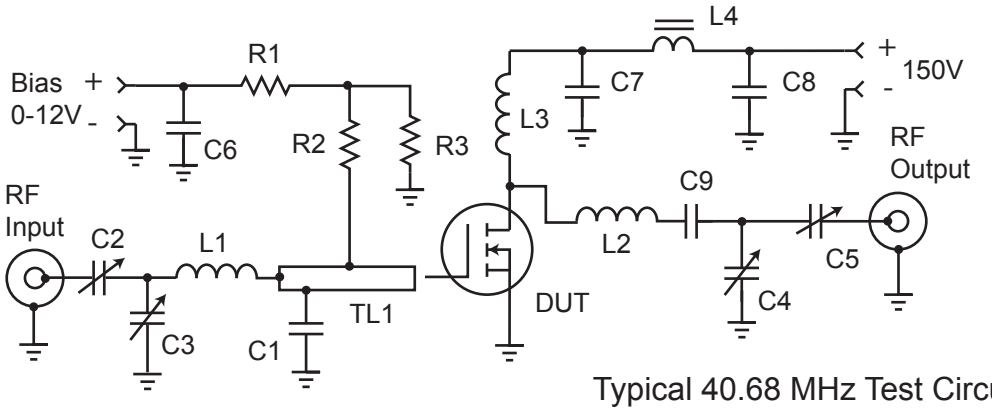


Figure 6b, TRANSIENT THERMAL IMPEDANCE MODEL

Table 1 - Typical Class AB Large Signal Input - Output Impedance

Freq. (MHz)	Z_{in} (Ω)	Z_{OL} (Ω)
2.0	18 - j 10.8	30 - j 1.5
13.5	1.3 - j 4.8	26- j 9.6
27.1	0.4- j 2.4	18 - j 13.1
40.7	0.2 - j 1.4	12 - j 12.4

Z_{IN} - Gate shunted with 25Ω I_{dq} = 100mA
Z_{OL} - Conjugate of optimum load for 300 Watts output at V_{dd}=150V



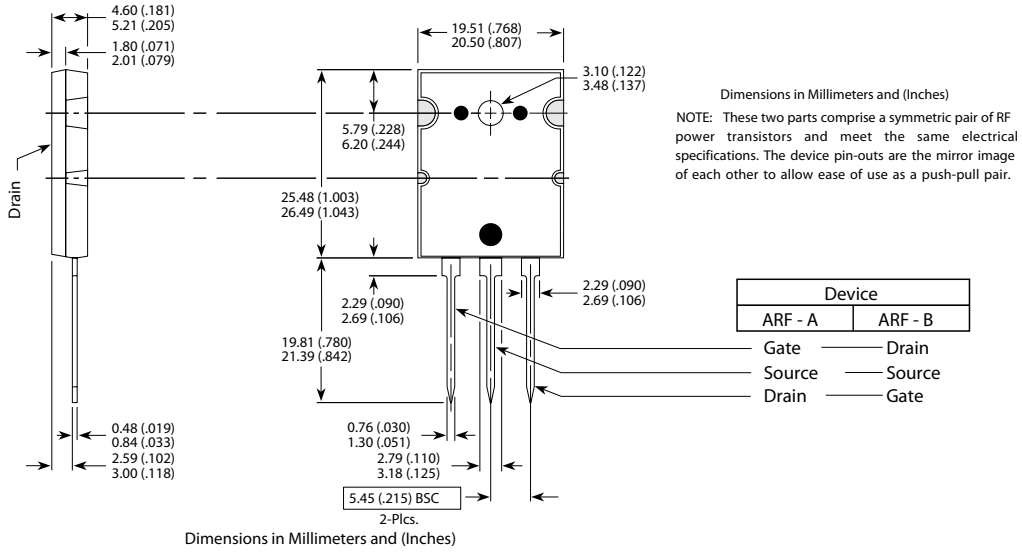
Typical 40.68 MHz Test Circuit

C1 -- 2200pF ATC 700B
C2-C5 -- Arco 465 Mica trimmer
C6-C8 -- .1 µF 500V ceramic chip
C9 -- 3x 2200 pF 500V chips COG

L1 -- 4t #22 AWG .25"ID .25 "L ~87nH
L2 -- 5t #16 AWG .312" ID .35"L ~176nH
L3 -- 10t #24 AWG .25"ID ~.5µH
L4 -- VK200-4B ferrite choke 3µH

R1- R3 -- 1kΩ 0.5Ω Carbon
TL1 -- 34Ω t-line 0.175" x 1"
C1 .45" from gate pin.
PCB -- 0.062" FR4, Er=4.7

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)

NOTE: These two parts comprise a symmetric pair of RF power transistors and meet the same electrical specifications. The device pin-outs are the mirror image of each other to allow ease of use as a push-pull pair.

Device	
ARF - A	ARF - B
Gate	Drain
Source	Source
Drain	Gate

Dimensions in Millimeters and (Inches)

050-4983 Rev A 4-2016